EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	135	"6323108"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:09
L2	13	("5013681" | "5024723" | "5303255" | "5374564" | "5540785" | "5646058" | "5681775" | "5757038" | "5877070" | "5882987" | "5953620" | "5980633" | "6004865").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:39
L3	6	"5888297"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:42
L4	46	"4771016"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:46
L5	103562	("10 nm" or "10nm")	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:47
L6	6	4 and 5	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:47
L7	5	"6030556"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 15:01
S1	2	("5948470").PN. or ((2002/042027) or (2002/005391)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 12:45
S2	0	(2002/042027).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:35
S3	0	2002/042027	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:35
S4	0	2002/042027	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:36
S5	0	(stephen chou).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:36

S6	4	("2002042027").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:37
S7	89	(stephen near chou).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:43
S8	0	S7 and @pd="02200411"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:44
S9	0	(2002/0005391).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:46
S10	0	(2002/005391).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:46
S11	0	2002/005391	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:46
S12	0	2002/0005391	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:47
S13	0	thurn-albrect.inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:47
S14	10	(thurn-albrecht).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:48

S15	75	"5948470"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:50
S16	2	("5948470").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:50
S17	0	(wo01/33300).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:50
S18	20	01/33300	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:51
S19	0	("wo20010500").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:52
S20	117005	"20010500"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:53
S21	0	wo?20010500	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:53
S22	0	wo20010500	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:53
S23	2	("7082876").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:54

S24	0	WO "20010500"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:26
S25	0	method of reducing pattern distortions during imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:30
S26	15	reducing pattern distortions during imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:31
S27	1	wo-0133300-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:32
S28	2	de-10030016-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:34
S29	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:04
S30	1308003	template or mold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:05
S31	7481	S30 near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:06
S32	289533	silicon near3 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:06

S33	436	S31 with (polymer or pmma or pmgi or photoresist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:07
S34	168	S29 and S30 and S33	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:07
S35	798153	nanometer or nm or nanoprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:09
S36	48	S34 and S35	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:09
S37	28	S29 and S33 and S32 and S35	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:14
S38	3465	(ge or germanium) near semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:06
S39	126033	semiconductor adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:06
S40	207948	silicon near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:07
S41	798313	nm or nanometer or nanoprint or nanoimprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:08

S42	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:09
S43	3465	(ge or germanium) near semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S44	126033	semiconductor adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S45	798313	nm or nanometer or nanoprint or nanoimprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S46	0	S43 and S44 and s "40" and S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S47	207948	silicon near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S48	322	S43 and S44 and S47 and S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S49	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:12
S50	93	S48 and S49	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:12

S51	28	S50 and (pmma or polymer or photoresist or pmgi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:13
S52	226110	template	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:32
S53	55209	S52 and "43" and "45" and "51"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:33
S54	3465	(ge or germanium) near semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S55	126033	semiconductor adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S56	798313	nm or nanometer or nanoprint or nanoimprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S57	207948	silicon near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S58	322	S54 and S55 and S57 and S56	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S59	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34

S60	93	S58 and S59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S61	28	S60 and (pmma or polymer or photoresist or pmgi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S62	0	S52 and S54 and S56 and S61	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S63	463	(silicon near substrate) and (polymer or pmma or pmgi or photoresist) and (semiconductor near (ge or germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:36
S64	159	S63 and S59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:37
S65	13	S60 and (pmma or polymer or pmgi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:47
S66	346	S59 and S56 and S52 and S57 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:48
S67	4630	(((nano?imprint$3) or (nano imprint $3) or (imprint adj lithograp$6)) or nanolithograp$5 or (nano?lithogra $6))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:34
S68	1602236	germanium or ge	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:35

S69	268466	(pmma or polymethylmeth$ or pmgi or polymethylgluta$ or az5214e or photoresist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:38
S70	1112	S67 and S68	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:38
S71	101	S67 same S68	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:38
S72	1540	S67 and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:41
S73	480	S67 same S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S74	26586	S68 and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S75	3507	S68 same S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S76	10	S71 and S73 and S75	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S77	65	shunpu.inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 11:21

S78	19543	template.ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 11:21
S79	4	S78 and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 11:21
S80	3	("4407695" | "4512848" | "4801476").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/21 12:38
S81	34806	germanium with (aluminum or al or indium or gold)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:15
S82	5375	(germanium with (aluminum or al or indium or gold)) with semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:16
S83	30322507	@ad<"20050513"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:20
S84	3671	S82 and S83	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:20
S85	92	S84 and substrate and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:20
S86	505	(((germanium with (aluminum or al or indium or gold)) with semiconductor) with substrate) and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:31
S87	938302	"427".clas. or "428".clas. or "430".clas. or "425".clas. or "264".clas. or "156".clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:35

S88	572282	S83 and S87	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:36
S89	2	("4512848").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/21 14:41
S90	483	photoresist and template and silicon and germanium and S69 and pattern and (nanometer or angstrom or nm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 15:03
S91	108	S90 and S88	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 15:04
S92	108	S91 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 15:13
S93	268466	(pmma or polymethylmeth$ or pmgi or polymethylgluta$ or az5214e or photoresist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S94	30322507	@ad<"20050513"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S95	938302	"427".clas. or "428".clas. or "430".clas. or "425".clas. or "264".clas. or "156".clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S96	572282	S94 and S95	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12

S97	483	photoresist and template and silicon and germanium and S93 and pattern and (nanometer or angstrom or nm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S98	108	S97 and S96	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S99	108	S98 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S100	34	S99 and (imprint with lithography)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S101	34	(US-20060076717-$ or US-20060062867-$ or US-20060035164-$ or US-20040141168-$ or US-20040124566-$ or US-20040086793-$ or US-20040053146-$ or US-20040022888-$ or US-20040021254-$ or US-20040007799-$ or US-20030205658-$ or US-20030205657-$ or US-20020115002-$ or US-20020098426-$ or US-20020094496-$ or US-20020093122-$).did. or (US-7374968-$ or US-7338275-$ or US-7229273-$ or US-7179079-$ or US-7140861-$ or US-7132225-$ or US-7077992-$ or US-7070405-$ or US-7037639-$ or US-7027156-$ or US-6954275-$ or US-6932934-$ or US-6926921-$ or US-6921615-$ or US-6919152-$ or US-6916585-$ or US-6916584-$ or US-6696220-$).did.	US-PGPUB; USPAT	ADJ	ON	2008/07/21 17:28
S102	34	S101 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:29

S103	1	S102 not (silicon adj germanium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:31
S104	1	S103 and germanium and S93 and S97	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:35
S105	13	("20030213382" | "20040163758" | "5512131" | "6060121" | "6365059" | "6407443" | "6518194" | "6547940" | "6599824" | "6709929" | "6755984" | "6764833" | "7060625").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/22 07:59
S106	5	"6506660"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 08:08
S107	34	(US-20060076717-$ or US-20060062867-$ or US-20060035164-$ or US-20040141168-$ or US-20040124566-$ or US-20040086793-$ or US-20040053146-$ or US-20040022888-$ or US-20040021254-$ or US-20040007799-$ or US-20030205658-$ or US-20030205657-$ or US-20020115002-$ or US-20020098426-$ or US-20020094496-$ or US-20020093122-$).did. or (US-7374968-$ or US-7338275-$ or US-7229273-$ or US-7179079-$ or US-7140861-$ or US-7132225-$ or US-7077992-$ or US-7070405-$ or US-7037639-$ or US-7027156-$ or US-6954275-$ or US-6932934-$ or US-6926921-$ or US-6921615-$ or US-6919152-$ or US-6916585-$ or US-6916584-$ or US-6696220-$).did.	US-PGPUB; USPAT	ADJ	ON	2008/07/22 09:59
S108	34	S107 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 09:59

S109	1666	germanium with sputter$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 10:17
S110	26	S109 and silicon and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 10:17
S111	34	S107 and nm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:33
S112	16	S107 and (layer with nm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:34
S113	7	S107 and ((thick or thickness) with nm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:37
S114	0	S107 and ((thick or thickness) with (mask or polymer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:39
S115	0	S107 and ((thick or thickness) with (resist))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:39
S116	4	S107 and ((thick or thickness) with ($resist))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:40
S117	3	S107 and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:03

S118	1	S107 and polymethylmethacrylate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:04
S119	25	(US-20020042027-$ or US-20020005391-$ or US-20030205658-$ or US-20030205657-$ or US-20050281982-$ or US-20050221218-$ or US-20040141168-$ or US-20040124566-$ or US-20040086793-$ or US-20040053146-$ or US-20040053009-$ or US-20020168592-$ or US-20020115002-$ or US-20020094496-$ or US-20060035164-$ or US-20040170925-$).did. or (US-5948470-$ or US-6753130-$ or US-4512848-$ or US-7374968-$ or US-7060625-$ or US-6755984-$ or US-6365059-$ or US-5512131-$).did. or (US-5948470-$ or WO-0133300-A-$ or DE-10030016-A-$).did.	US-PGPUB; USPAT; DERWENT	ADJ	ON	2008/07/22 13:07
S120	10	S119 and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:08
S121	23	S119 and nm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:15
S122	1	("20030071016").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/22 16:23
S123	199	(lee near heon).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:42
S124	15	S123 and silicon and substrate and pattern and imprint	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:43
S125	177981	"430".clas. or "216".clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:47

S126	533	S125 and silicon and substrate and pattern and imprint	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:47
S127	190	S126 and template	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:48
S128	32	S127 and imprint pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:49
S129	5	2003/0071016	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:52
S130	2	"20030071016"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:52
S131	456	nano?imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:00
S132	17	S131 and (silicon near substrate) and (imprint pattern)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:01
S133	53	"6165911"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:05
S134	4	"6673714"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:07

S135	12064	"Hewlett-Packard Development ". asn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:32
S136	53	"6165911"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:32
S137	17	S135 and S136	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:32
S138	456	nano?imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
S139	17	S138 and (silicon near substrate) and (imprint pattern)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
S140	0	S135 and S139	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
S141	15	S135 and S138	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
S142	5	S135 and (silicon near substrate) and (imprint pattern)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:34
S143	202	ingenia.asn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 08:41

S144	136401	S143 and semiconductor or imprint or lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 08:42
S145	12	S143 and (semiconductor or imprint or lithography)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 08:42
S146	23	((SHUNPU) near2 (LI)).INV.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/23 09:50
S147	32	((SHUNPU) near2 (LI)).INV.	EPO; JPO; DERWENT	ADJ	ON	2008/07/23 09:51
S148	55	S146 or S147	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 09:51
S149	22523	(single?phase)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:18
S150	72	(single?phase polymer)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:18
S151	1	(single?phase plastic)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:19
S152	32	(single?phase layer)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:19
S153	105	S150 or S151 or S152	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:19
S154	4559269	@ad<"20031211"	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:20
S155	84	S153 and S154	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:20
S156	26	S155 and substrate	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:21
S157	0	S155 and template	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:21
S158	27	shunpu.inv.	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:22
S159	60563	(single phase) or (single-phase)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:24
S160	219	(single phase polymer) or (single-phase polymer)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:25
S161	9	(single phase plastic) or (single-phase plastic)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:25
S162	228	S160 or S161	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:25
S163	65	S162 and (template or substrate)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:25
S164	30	S163 and S154	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:26

S165	0	S164 and shunpu.inv.	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:26
S166	37	substrate and pmmi	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:55
S167	25887	substrate and polymer and (texture or textured)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:57
S168	318158	tg or glass transition	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:57
S169	7874	below (tg or glass transition)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:58
S170	509	S167 and S169	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:58
S171	37644	polymer layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:59
S172	122	S170 and S171	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:59
S173	25	(US-20020042027-$ or US-20020005391-$ or US-20030205658-$ or US-20030205657-$ or US-20050281982-$ or US-20050221218-$ or US-20040141168-$ or US-20040124566-$ or US-20040086793-$ or US-20040053146-$ or US-20040053009-$ or US-20020168592-$ or US-20020115002-$ or US-20020094496-$ or US-20060035164-$ or US-20040170925-$).did. or (US-5948470-$ or US-6753130-$ or US-4512848-$ or US-7374968-$ or US-7060625-$ or US-6755984-$ or US-6365059-$ or US-5512131-$).did. or (US-5948470-$ or WO-0133300-A-$ or DE-10030016-A-$).did.	US-PGPUB; USPAT; DERWENT	ADJ	ON	2009/04/30 15:14
S174	1	S173 and S169	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:15
S175	6	S173 and S168	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:15
S176	245154	"428".clas.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:19
S177	55	S172 and S176	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:19
S178	0	("2005/0281982").URPN.	USPAT	ADJ	ON	2009/04/30 15:30
S179	2110815	template or stamp or stamper or press or die or mold	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:31
S180	2589840	layer or substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:31
S181	1012394	polymer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:31
S182	324457	S179 and S180 and S181	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:31

S183	3298	S182 and S169	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:33
S184	451	S183 and S171	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:34
S185	3	S184 and "249".clas.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:36
S186	91799	germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:57
S187	35821	pmma	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:57
S188	1731	S186 and S187	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:57
S189	48253	germanium and semiconductor and substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:58
S190	1098	S188 and S189	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:58
S191	83956	texture and (bake or baking or heat or heating or heated)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:58
S192	63	S190 and S191	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:58
S193	0	master and resist and germanuim and (@ay<"2003" or @prad<"20030101" or @py<"2003")	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:36
S194	0	master and resist and germanuim	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:36
S195	2760	master and germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:37
S196	734	S195 and resist	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:37
S197	393	S196 and (@ay<"2003" or @prad<"20030101" or @py<"2003")	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:37
S198	73	S197 and pmma	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:37
S199	67	S198 and (heat or temperature or bake or heated or baked)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:38
S200	67	S199 and substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:39
S201	1	S199 and pmma layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:39
S202	6	("4098917" | "4127414" | "4188215" | "4256825" | "4269935" | "4276368").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:40
S203	18	("4373018").URPN.	USPAT	ADJ	ON	2009/05/01 09:41
S204	109	977/887.ccls.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:47
S205	156504	substrate and (anneal or anneal$)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:48
S206	5	S204 and S205	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:48

S207	2619	S205 and pmma	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:56
S208	20706	S205 and germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:57
S209	2784	germanium near substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:57
S210	1274	S208 and S209	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:57
S211	3530331	(heat or temperature or bake or heated or baked)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:58
S212	1189	S210 and S211	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:58
S213	154	S212 and polymer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:59
S214	266679	textu$	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 11:00
S215	170767	texture	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 11:00
S216	10	S213 and S214	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 11:00
S218	1850800	template or imprint or stamp or press or mask	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 11:03
S219	130	S213 and S218	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 11:03
S220	5079	S208 and polymer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 12:03
S221	373	S220 and polymer layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 12:03
S222	144062	S205 and S211	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 13:03
S223	2820	S222 and polymer layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 13:03
S224	362	S223 and germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 13:03
S225	1488	425/385.ccls.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 14:37
S226	10	S225 and germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 14:37
S227	20	S225 and annea$	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 14:40
S228	32	("20020185584" | "20030080458" | "20030209819" | "20040029041" | "20040036201" | "20040039090" | "20040131718" | "20040146792" | "20040169861" | "20040233442" | "20040233443" | "20040233444" | "20040259279" | "20050067379" | "20050133954" | "20050179149" | "20060183060" | "5204126" | "6429932" | "6517995" | "6607173" | "6632342" | "6656393" | "6713238" | "6921630" | "6936181" | "6949199" | "7013064" | "7070405" | "7077992" |	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 14:52

		"7136150" | "7235474").PN.				
S229	4622	((425/171) or (425/174) or (425/174.4) or (264/1.38) or (425/385) or (425/169) or (425/173)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/12 10:03
S230	97200	pmgi or polymethylgluta$ or poly methyl glutar$ or polymethyl glutar$ or poly methylglutar$ or pmma or poly methyl methacrylate or poly methylmethacrylate or polymethyl methacrylate or polymethylmethacrylate or (photoresist (az-5214$ or az5214$ or az "5214"$ or az-5214 or az "5214" or az5214))	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 10:27
S231	92066	germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 10:27
S232	7	S229 and S230 and S231	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 10:27
S233	241280	anneal or anneal$	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 12:25
S234	4622	((425/171) or (425/174) or (425/174.4) or (264/1.38) or (425/385) or (425/169) or (425/173)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/12 12:25
S235	97200	pmgi or polymethylgluta$ or poly methyl glutar$ or polymethyl glutar$ or poly methylglutar$ or pmma or poly methyl methacrylate or poly methylmethacrylate or polymethyl methacrylate or polymethylmethacrylate or (photoresist (az-5214$ or az5214$ or az "5214"$ or az-5214 or az "5214" or az5214))	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 12:26
S236	24	S233 and S234 and S235	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 12:26
S237	156837	S233 and substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 12:42
S238	49764	S237 and (mold or template or stamp or stamper)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 13:02
S239	2676	S238 and S235	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 13:02
S240	13	S239 and S234	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 13:02
S241	8129	S233 near (polymer or plastic or template or semiconductor or mold)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 14:30
S242	275	S241 and ("264".clas. or "425".clas.)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 14:30
S243	0	(2002/0042027).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/12 14:44
S244	58	2002/0042027	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 14:44
S245	0	2002/0042027.pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 14:46

S246	541	"5772905"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 15:01
S247	1	"5772905".pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 15:01
S248	1	"6849558".pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:24
S249	1	"6755984".pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:26
S250	103562	"10 nm" or "10nm"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:33
S251	3552	S250 near (substrate or layer or semiconductor or germanium or silicon or wafer)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:33
S252	40	S251 and chou	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:34
S253	131	"5259926"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:37
S254	940	S250 near (substrate or semiconductor or germanium or silicon or wafer)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:44
S255	332	S250 near substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:44
S256	65	S250 near semiconductor	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:45
S257	1199	S250 and ("264".clas. or "425". clas.)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:49
S258	1076	S257 and (substrate or layer or semiconductor)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:50
S259	780	S258 and substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:50
S260	718	S259 and layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:50
S261	280	S260 and semiconductor	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:50
S262	79	S261 and chou	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:50
S263	5468	("10 nm" or "10nm") with semiconductor	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:52
S264	2526	("10 nm" or "10nm") with semiconductor with layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:52
S265	8	S264 and chou	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:52

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